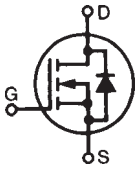
IXYS

Polar™ Power MOSFET
HiPerFET™

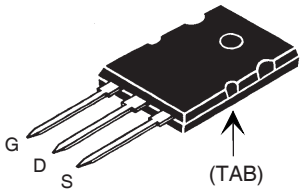
IXFK26N100P
IXFX26N100P

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

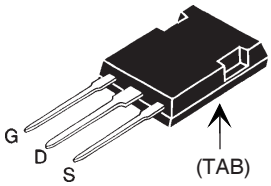


V_{DSS} = 1000V
I_{D25} = 26A
$R_{DS(on)}$ ≤ 390mΩ
t_{rr} ≤ 300ns

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	1000	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T_C = 25°C	26	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	65	A
I_{AR}	T_C = 25°C	13	A
E_{AS}	T_C = 25°C	1	J
dV/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le$ 150°C	15	V/ns
P_D	T_C = 25°C	780	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
M_d	Mounting torque (IXFK)	1.13/10	Nm/lb.in.
F_C	Mounting force (IXFX)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	TO-247	6	g

Symbol	Test Conditions	Characteristic Values (T_J = 25°C unless otherwise specified) Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	1000			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1mA	3.5		6.5	V
I_{GSS}	V_{GS} = ± 30V, V_{DS} = 0V			± 200	nA
I_{DSS}	V_{DS} = V_{DSS}			25	μA
	V_{GS} = 0V T_J = 125°C			2	mA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5 • I_{D25}, Note 1			390	mΩ

Features
- Fast intrinsic diode
- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

Advantages
- Easy to mount
- Space savings
- High power density

Applications:
- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

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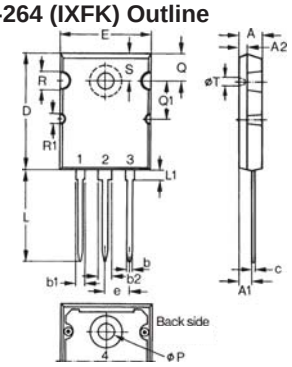
Symbol	Test Conditions (T_J = 25°C unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS}= 20V, I_D = 0.5 • I_{D25}, Note 1	13	22		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		11.9		nF
C_{oss}			690		pF
C_{rss}			60		pF
R_{Gi}	Gate input resistance		1.50		Ω
$t_{d(on)}$	**Resistive Switching Times**		45		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		45		ns
$t_{d(off)}$	R_G = 1Ω (External)		72		ns
t_f			50		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		197		nC
Q_{gs}			76		nC
Q_{gd}			85		nC
R_{thJC}				0.16	°C/W
R_{thCS}			0.15		°C/W

Source-Drain Diode — Characteristic Values (T_J = 25°C unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.	
I_S	V_{GS} = 0V			26	A
I_{SM}	Repetitive, pulse width limited by T_{JM}			104	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 13A, -di/dt = 100A/μs			300	ns
Q_{RM}	V_R = 100V, V_{GS} = 0V		1.2		μC
I_{RM}			12		A

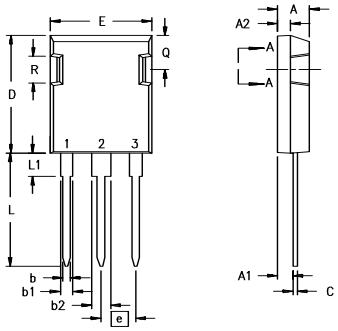
Note 1: Pulse test, t ≤ 300μs; duty cycle, d ≤ 2%.

TO-264 (IXFK) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS 247™ (IXFX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25ºC

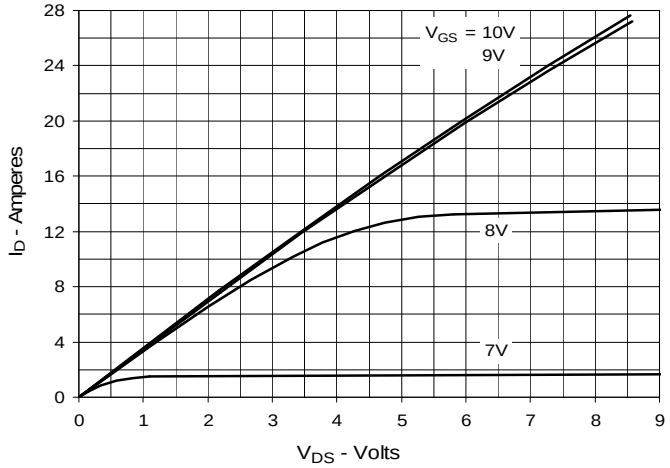


Fig. 2. Extended Output Characteristics @ 25ºC

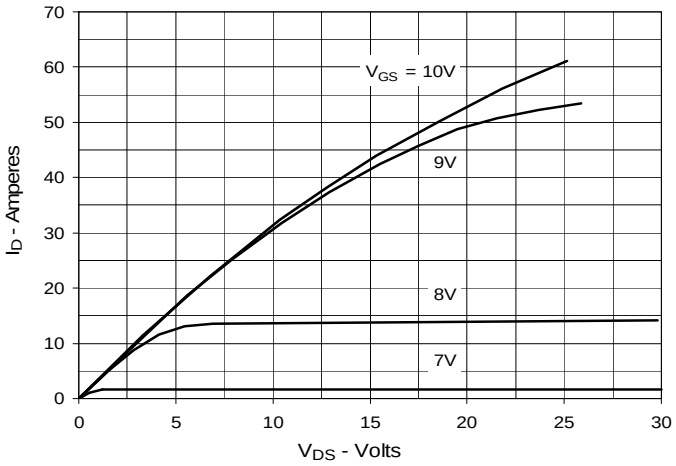


Fig. 3. Output Characteristics @ 125ºC

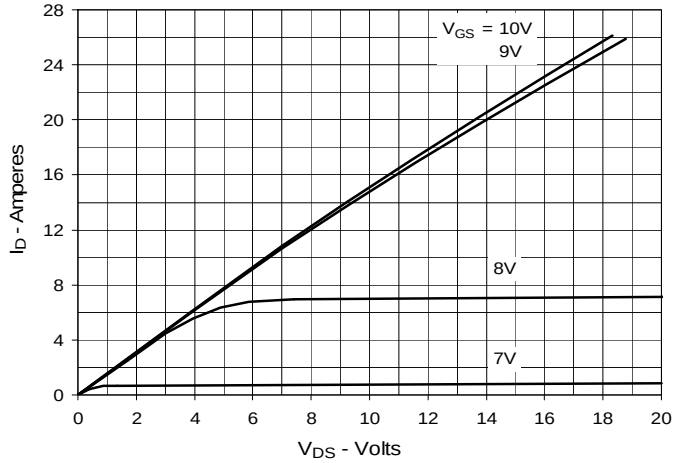


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 13A Value vs. Junction Temperature

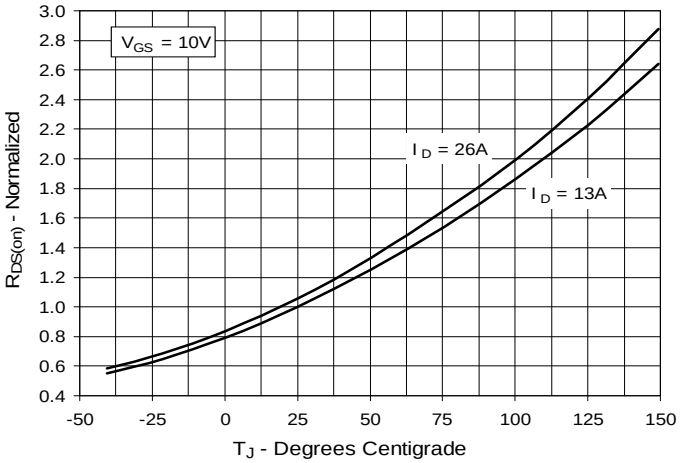


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 13A Value vs. Drain Current

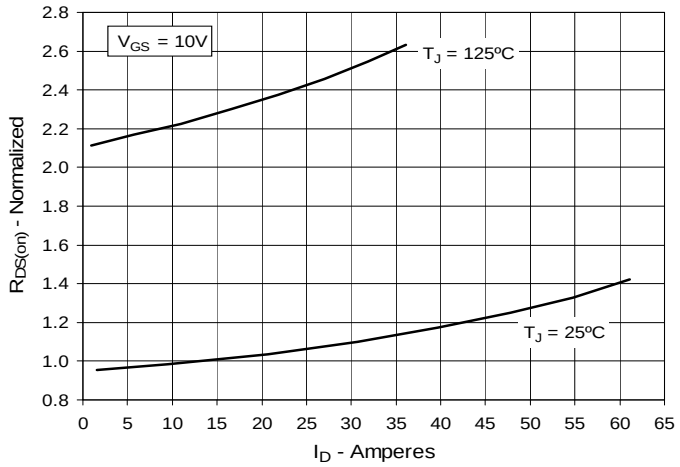


Fig. 6. Maximum Drain Current vs. Case Temperature

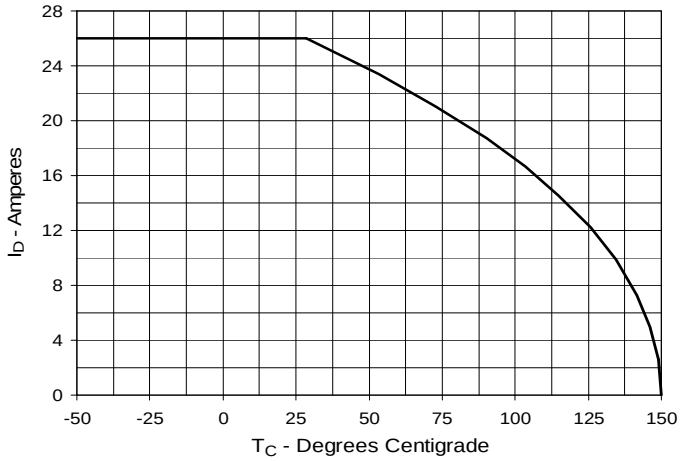


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Fig. 7. Input Admittance

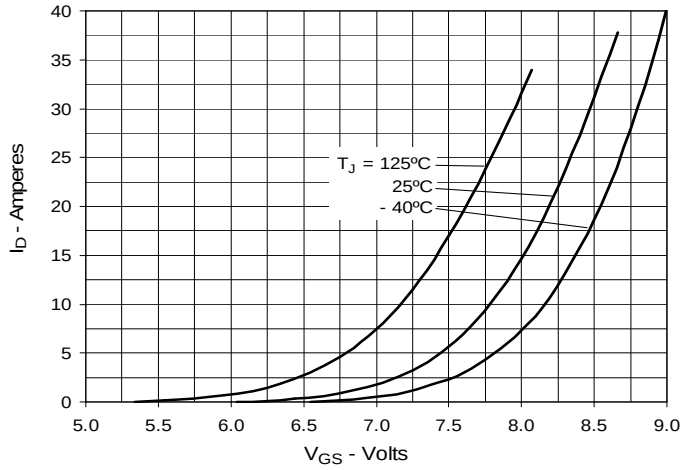


Fig. 8. Transconductance

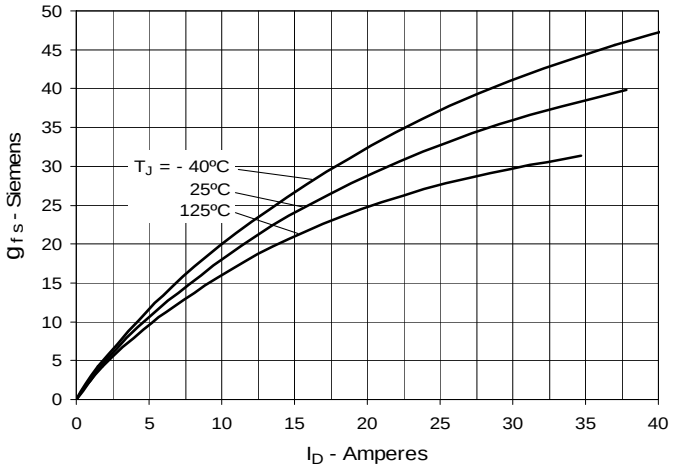


Fig. 9. Forward Voltage Drop of Intrinsic Diode

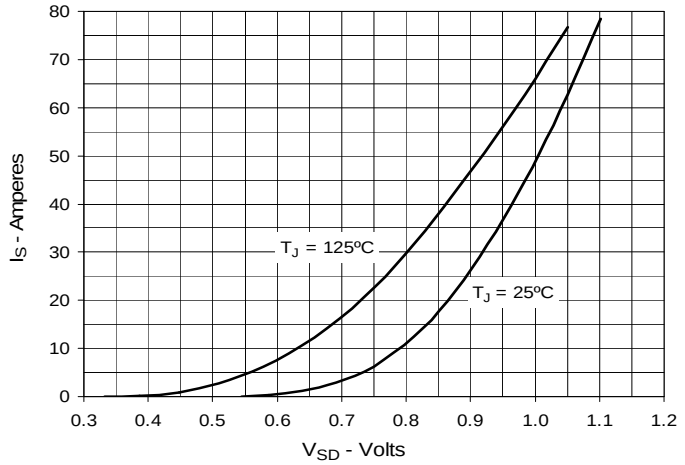


Fig. 10. Gate Charge

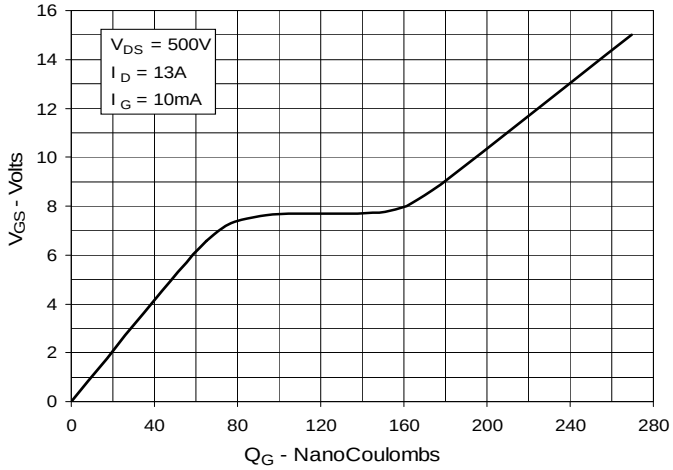


Fig. 11. Capacitance

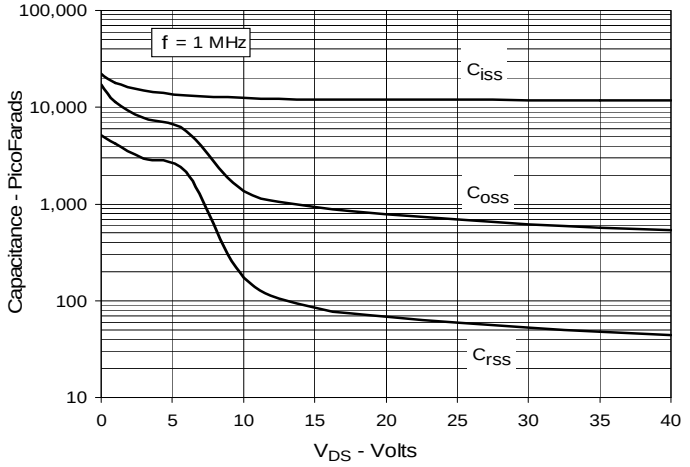
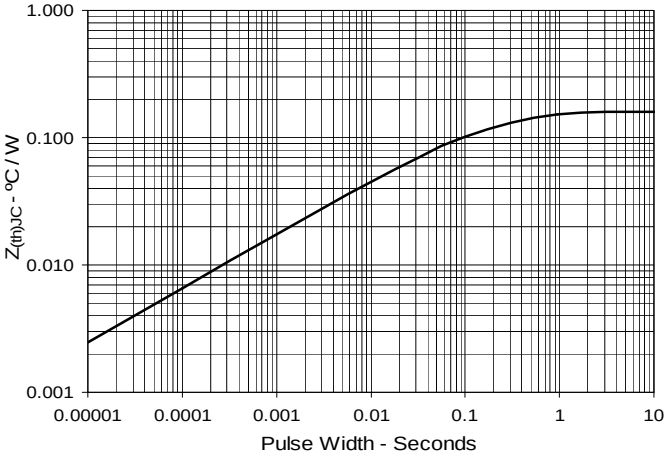


Fig. 12. Maximum Transient Thermal Impedance



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